



3DK29-II



NPN Silicon High Frequency M-Power Switch Transistor

Features:

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation and high frequency switch, high frequency small signal amplification, low power source adjustment circuit.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications					Test Condition
			A	B	C	D	E	
Total Dissipation	P_{tot}	mW	1000					Ta=25°C
Max. Collector Current	I_{CM}	mA	1000					
Junction Temperature	T_{jm}	°C	175					
Storage Temperature	T_{stg}	°C	-55~+175					
C-B Breakdown Voltage	$V_{(BR)CBO}$	V	40	60	75	60	40	Ic=0.1mA
C-E Breakdown Voltage	$V_{(BR)CEO}$	V	30	45	60	45	30	
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	4					IE=0.1mA
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.4					Ic=500mA IB=50mA
Base- Emitter Saturation Voltage Drop	$V_{BE(sat)}$	V	1.2					
C-E Leakage Current	I_{CEO}	uA	1.0					VCE=20V
DC Current Gain	h_{FE}		Orange: 25~40, Yellow: 40~55, Green: 55~80 Blue: 80~120, Purple: 120~180					VCE=1V, Ic=500mA
Transition frequency	f_T	MHz	150					VCE=10V, Ic=50mA f=30MHz
Turn-on Time	t_{on}	ns	30					Ic=300mA IB1= IB2=30mA
Storage Time	t_s	ns	250		100			
Fall Time	t_f	ns	30					

Outline and Dimensions: